

Z0409

双向可控硅
TRIAC版本号
201603-A

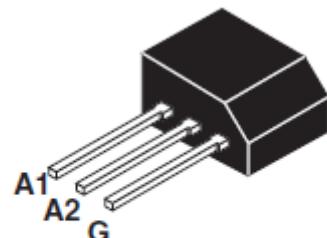
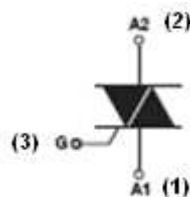
产品概述 GENERAL DESCRIPTION

Z0409 双向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

Z0409 Triacs is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
I _{T(RMS)}	4	A
V _{DRM/V_{RRM}}	600&800	V
I _{GT(IV)}	≤10	mA



TO202-3

产品特性 FEATURES

FEATURES

- dv/dt高
- 通态压降低
- Rohs环保产品
- Highly dv/dt
- Low on-state voltage
- Rohs Products

应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.

极限值(除非另有规定, $T_j=25^\circ\text{C}$) ABSOLUTE RATINGS

(Tj=25°C,unless otherwise specified)

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
I_{TRMS}	RMS 通态电流 RMS on-state current (full sine wave)	4	A
I_{TSM}	通态峰值浪涌电流 Non repetitive surge peak on-state current	25	A
I^2t	I^2t 耗散值 I^2t value for fusing	3.1	A^2s
di/dt	通态电流上升值 Critical rate of rise of on-state current	50	$\text{A}/\mu\text{s}$
I_{GM}	门极峰值电流 Peak gate current	2	A
$P_{G(AV)}$	平均门极耗散功率 Average gate power dissipation	0.5	W
T_{STG}	贮存结温范围 Storage junction temperature range	-40--150	°C
T_j	工作结温范围 Operating junction temperature range	-40--125	°C

电参数(除非另有规定, $T_j=25^\circ\text{C}$) ELECTRICAL CHARACTERISTICS

(Tj=25°C,unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value	单位 Unit	测试条件 Test Conditions
触发电流 Gate trigger current	I_{GT}	$I \sim IV$	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
触发电压 Gate trigger voltage	V_{GT}	$I \sim IV$	V	$V_D=12\text{V}, I_T=0.1\text{A}$
维持电流 Holding current		I_H	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
擎住电流 Latching current	I_L	I, III II, IV	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
电压上升率 Rise of off- state voltage		dv/dt	$\text{V}/\mu\text{s}$	$V_D=67\% V_{DRM}$
通态压降 Peak on-state voltage		V_{TM}	V	$I_T=5.5\text{A}$
断态漏电流 Peak repetitive forward blocking current	I_{DRM} I_{RRM}	≤ 5 ≤ 0.8	μA mA	$V_{RRM}=V_{DRM}, T_j = 25^\circ\text{C}$ $V_{RRM}=V_{DRM}, T_j = 125^\circ\text{C}$

热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter	数值 Value	单位 Unit
$R_{th(j-c)}$	Junction to case(AC)	15	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	Junction to ambient	100	$^\circ\text{C}/\text{W}$

特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与RMS通态电流关系
 Fig.1. Maximum Power Dissipation Versus on-state current

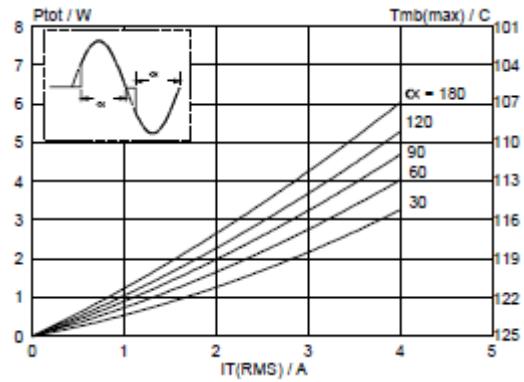


图3 通态特性
 Fig.3. On-State Characteristics

图2 RMS通态电流与Tc温度关系
 Fig.2. RMS On-state Current Versus TL

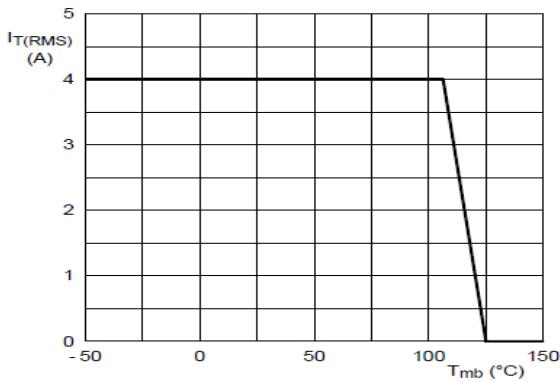


图4 通态浪涌峰值电流与周期数关系
 Fig.4. Surge Peak On-state Current Versus Number Cycles

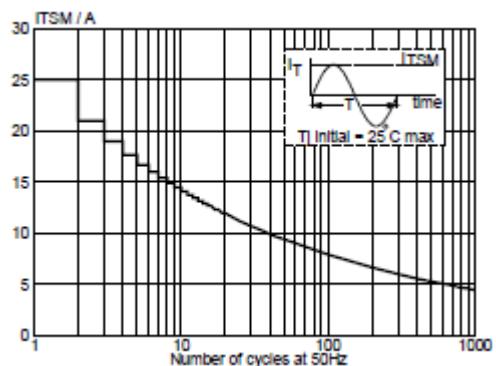
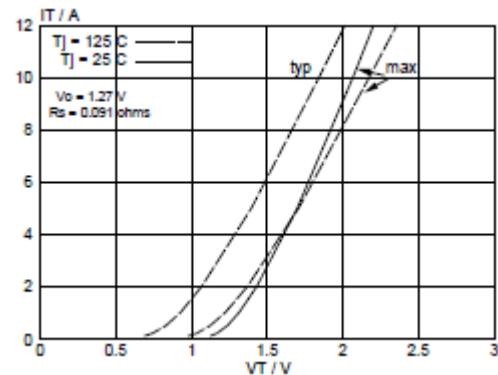
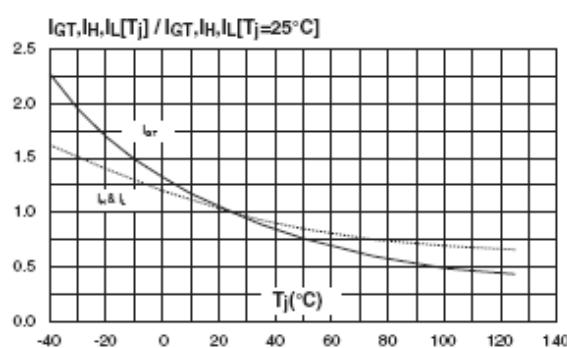
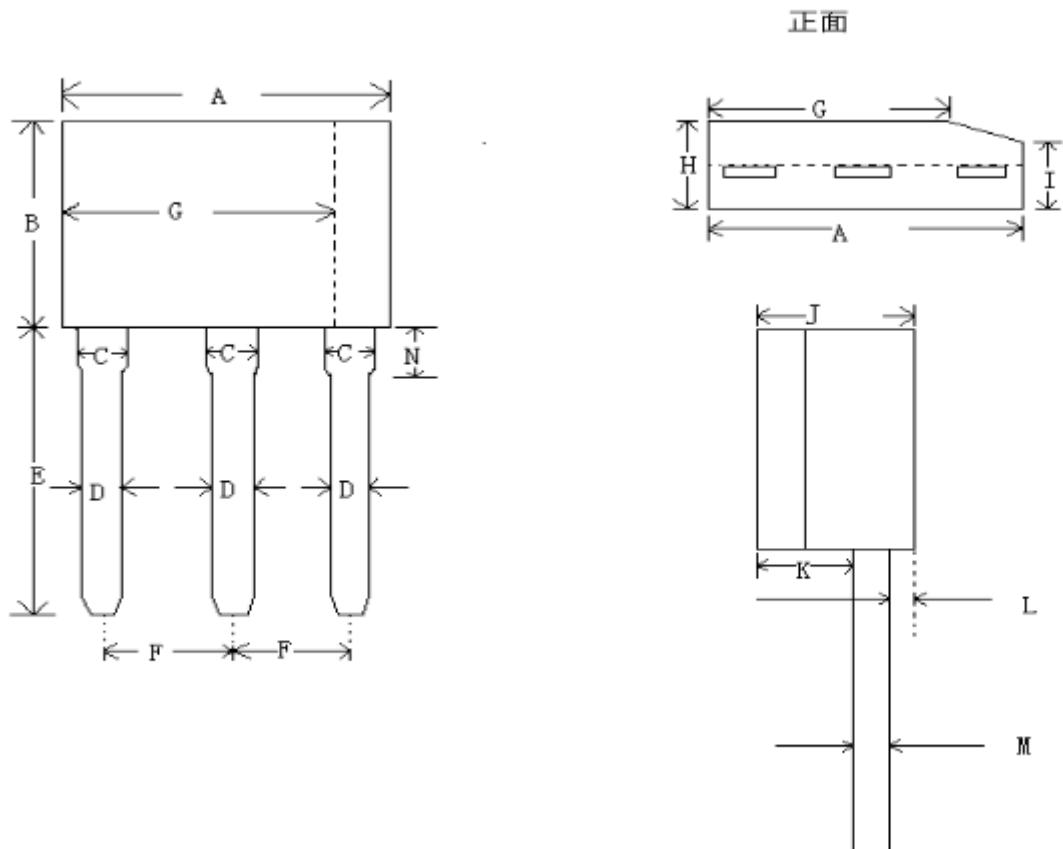


图5 IGT、IH、IL相对值（相对于25℃）与结温关系
 Fig.5. Relative Variation Of Gate Trigger Current , Holding Current And Latching Current Versus Junction Temperature (Typical Value)



封装尺寸 PACKAGE MECHANICAL DATA
TO-202-3


代码	最小值	最大值	代码	最小值	最大值
A	9.10	10.10	B	6.70	7.70
C	1.17	1.47	D	0.57	0.87
E	9.90	11.90	F	2.39	2.69
G	7.00	8.00	H	4.06	5.06
I	2.10	3.10	J	4.06	5.06
K	2.10	2.60	L	1.40	1.90
M	0.35	0.65	N	1.50	2.50

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